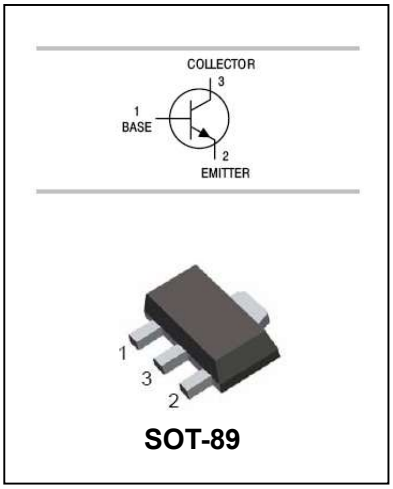
NPN Silicon Epitaxial Planar Transistor 2SC4374

FEATURES

- Complementary to 2SA1662

Lead-free



SOT-89

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC4374	EO/EY	SOT-89

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	0.4	A
P_C	Collector Power Dissipation	500	mW
T_j,T_{stg}	Junction and Storage Temperature	-55 to +150	℃

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ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=1mA,I_E=0	80			V
Collector- emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	80			V
Emitter- base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=80V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=2V,I_C=50mA	70		240	
		V_{CE}=2V,I_C=200mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=200mA,I_B=20mA			0.4	V
Base-emitter	V_{BE}	V_{CE}=-2V,I_C=5mA	0.55		0.8	V
Transition frequency	f_T	V_{CE}=10V, I_C=10mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		14		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240
Marking	EO	EY

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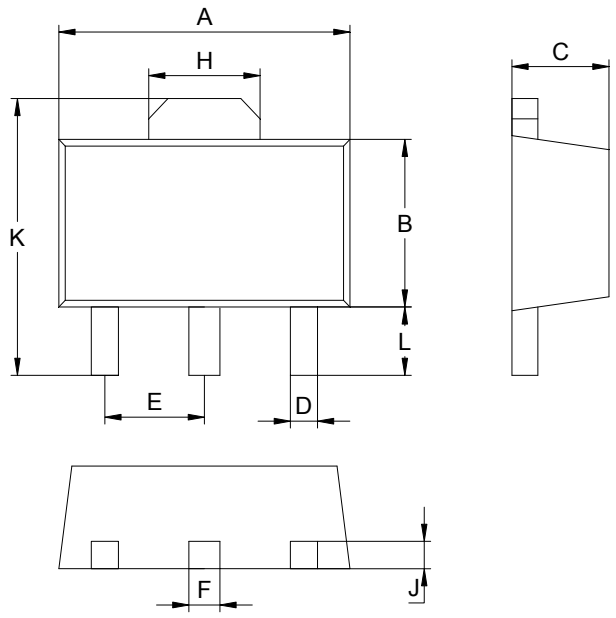
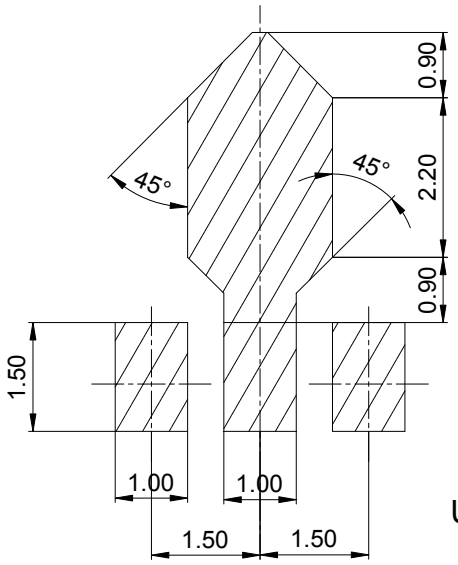
PACKAGE OUTLINE

Plastic surface mounted package SOT-89



SOT-89		
Dim	Min	Max
A	4.30	4.70
B	2.25	2.65
C	1.50 Typical	
D	0.40 Typical	
E	1.40	1.60
F	0.48 Typical	
H	1.60	1.80
J	0.40 Typical	
L	0.90	1.10
K	3.95	4.35
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit:mm

PACKAGE INFORMATION

Device	Package	Shipping
2SC4374	SOT-89	1000/Tape&Reel